

REMARKS

Allowable Subject Matter

The Examiner stated that claims 34-37, 39, and 47-51 are allowed.

The Examiner continued:

“Claim 61 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.”

With regard to claim 61, claim 61 has been rewritten in independent form including all of the limitations of the base claim. There were no intervening claims so claim 61 is now allowable.

The Examiner stated:

“The following is a statement of reasons for the indication of allowable subject matter: the examiner is unaware of any prior art which suggests or renders obvious a method of fabrication for an electrostatic discharge protection circuit that is formed at an input/output interface of an integrated circuit formed on a substrate which comprises a polycrystalline silicon bounded SCR (silicon controlled rectifier) having a well of a first conductivity type formed within a well of a second different conductivity type with the first well containing a region of the second conductivity type and the second well containing a region of the first conductivity type having a heavily doped polysilicon layer between these two regions and astride the junction between the two wells such that the SCR is connected between a signal input/output interface and power supply connection of the integrated circuit with a biasing circuit connected to the SCR in order to bias the SCR to turn on faster during an electrostatic discharge situation as suggested in claim 34. The examiner is also unaware of any prior art which suggests or renders obvious a method of fabrication for an electrostatic discharge protection circuit that is formed at an input/output interface of an integrated circuit formed on a substrate which comprises a shallow trench isolation bounded SCR (silicon controlled rectifier) that is connected between a signal input/output interface and power supply connection of the integrated circuit with a biasing circuit connected to the SCR in order to bias the SCR to turn on faster during an electrostatic discharge situation such that a diode on the substrate is connected between the signal input/output interface and the anode of the SCR in order to increase the holding voltage for the SCR when it is on as suggested in claim 61.”

Applicants respectfully submit that the claimed combinations including the above subject matter are allowable.

Claim Rejections - 35 USC §102

Claims 60 and 62 are rejected under 35 U.S.C. §102(b) as being anticipated by Kunz et al. (U.S. Appl. Pub. No. 2002/0145164 A1, hereinafter "Kunz").

With regard to claims 60 and 62, these claims have been canceled so these rejections are now moot.

Restriction/Election

The Examiner stated that claims 1-33, 38, 40-46, 52-59, 63, 64, and 66 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected species, there being no allowable generic or linking claim.

Claims 1-33, 38, 40-46, 52-59, 63, 64, and 66 have been canceled.

Claim Objections

Claim 62 is objected to because of the following informalities:

“...the phrase "forming a shallow trench isolation bounded diode said shallow trench isolation bounded diode" is unintelligible. Appropriate correction is required.”

With regard to claim 62, this claim has been canceled so the objection is now moot.

Specification

The Examiner stated that the title of the invention is not descriptive.

“A new title is required that is clearly indicative of the invention to which the claims are directed.”

A new title has been provided that is clearly indicative of the invention to which the claims are directed:

“METHOD FOR FORMING AN ESD PROTECTION CIRCUIT”

Claim Rejections - 35 USC §112

Claim 65 is rejected under 35 U.S.C. §112, second paragraph as being indefinite for failing to particularly point out and distinctly claim the subject matter which Applicant regards as the invention.

“Claim 65 recites the limitation "a second gate" in lines 5-6. There is insufficient antecedent basis for this limitation in the claim since a first gate is not defined in claim 60.”

With regard to claim 65, this claim has been canceled so the rejection is now moot.

Conclusion

In view of the above, it is submitted that the claims are in condition for allowance and reconsideration of the rejections is respectfully requested. Claims 34-37, 39, and 47-51 have been allowed and claim 61 has been amended to be allowable. Passage to grant at an early date is solicited.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including any extension of time fees, to Deposit Account No. 50-0374 and please credit any excess fees to such deposit account.

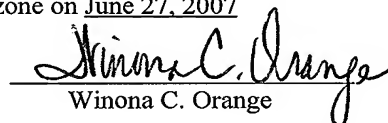
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